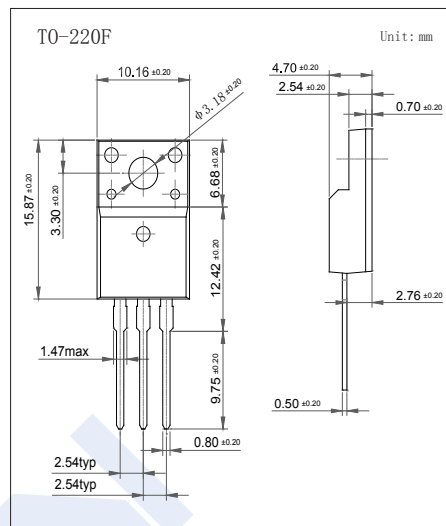
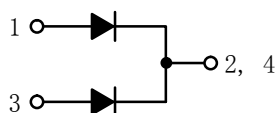


Schottky Barrier Diodes

MBR20100F

■ Features

- LOW V_F .
- High Operating Junction Temperature.
- High Switching Speed.
- High Reliability.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
DC Blocking Voltage @ $I_r=0.2\text{mA}$	V_{RRM}	100	V
DC Forward Current	$I_F(AV)$	10	A
Peak forward surge current	I_{FSM}	150	
Junction Temperature	T_J	175	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_{RM}	$I_R = 0.2 \text{ mA}$	100			V
Forward voltage	V_F	$I_F = 10 \text{ A}, T_c = 25^\circ\text{C}$ (Note.1)			850	mV
Reverse voltage leakage current	I_R	$V_R = 100\text{V}, T_c = 25^\circ\text{C}$ (Note.1)			10	μA

Note.1: Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

Schottky Barrier Diodes

MBR20100F

■ Typical Characteristics

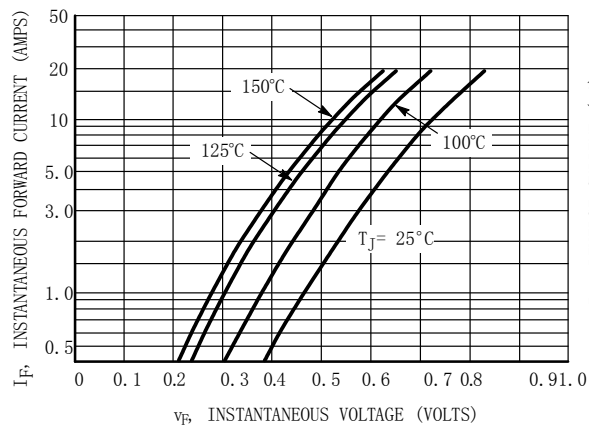


Figure 1. Typical Forward Voltage Per Diode

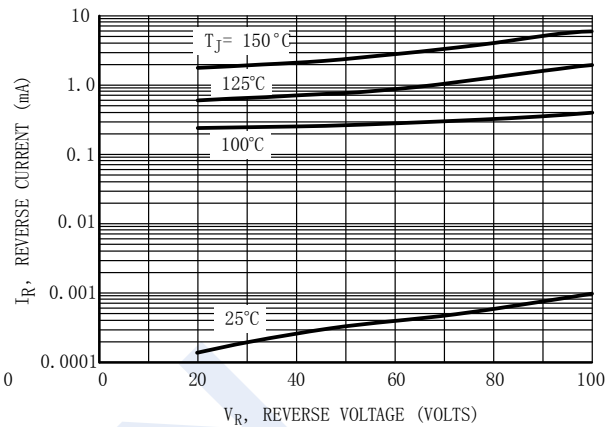


Figure 2. Typical Reverse Current Per Diode

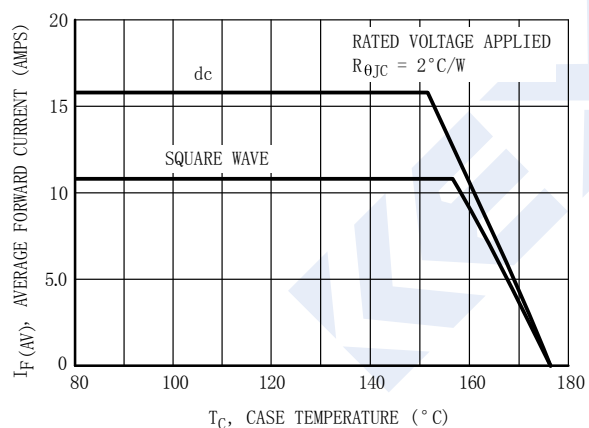


Figure 3. Typical Current Derating, Case, Per Leg

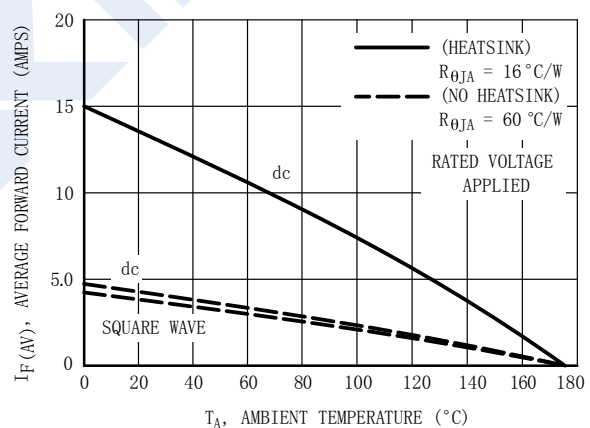


Figure 4. Typical Current Derating, Ambient, Per Leg

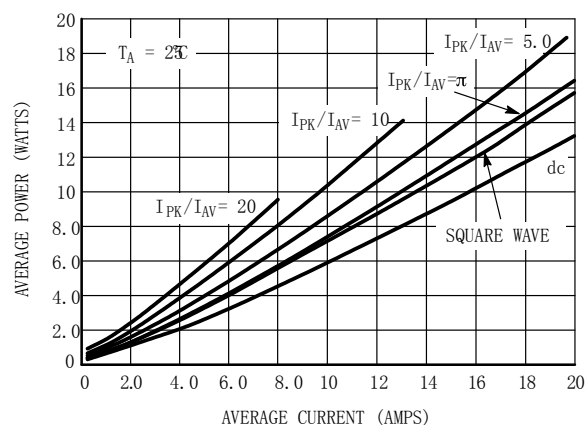


Figure 5. Average Power Dissipation and Average Current